

**IN THE SPECIFICATION:**

Please insert before the first paragraph under **BACKGROUND OF THE INVENTION** of page 1 of the Disclosure currently on file with the following paragraph:

This application is a Continuation application of U.S. Application No. 10/319,551 filed December 16, 2002, which is a Divisional application of U.S. Application 09/982,842 filed October 22, 2001. Priority is claimed based on U.S. Serial No. 10/319,551 filed on December 16, 2002, which claims the priority date of U.S. Application 09/982,842 filed October 22, 2001, which claims the priority date of Japanese Patent Application No. 2000-347096 filed November 14, 2000.

Please replace the first paragraph under **BACKGROUND OF THE INVENTION** of page 1 of the Disclosure currently on file with the following paragraph:

The present invention relates to a semiconductor integrated circuit device and a method of producing the same, specifically to a technique effective in application to a DRAM (Dynamic Random Access Memory) in which the bit lines of ~~minute~~ small line widths are formed with a conductive film ~~containing W (tungsten)~~ as the ~~principal component~~.